Fig. 1A

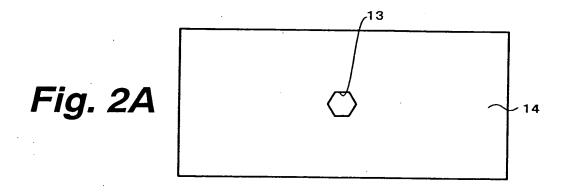
107(p)
104

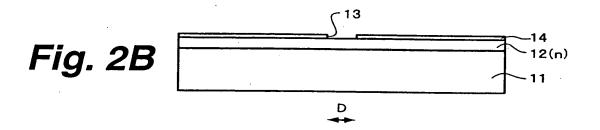
Fig. 1B

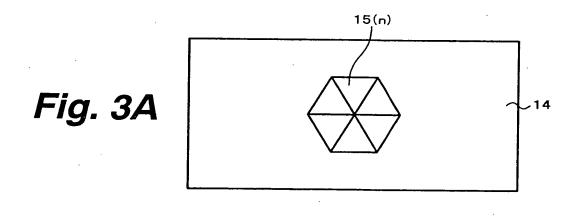
107(p)
106

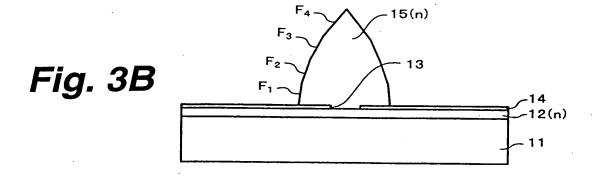
108

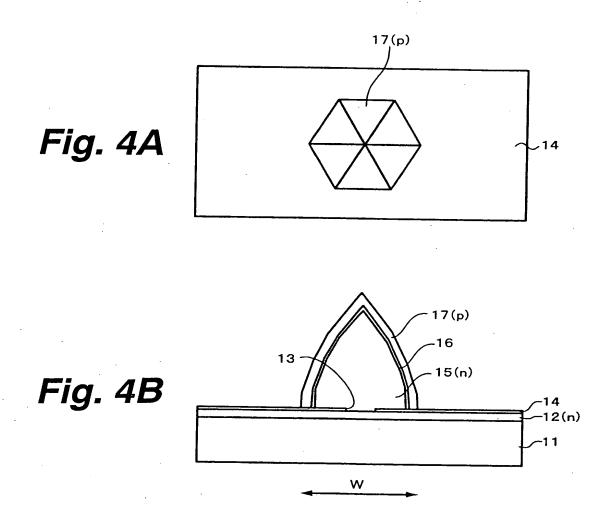
109
109
100
101











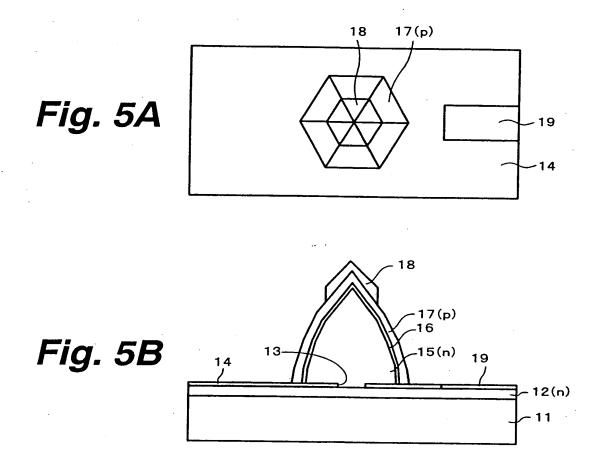


Fig. 6

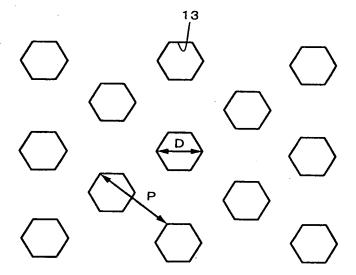
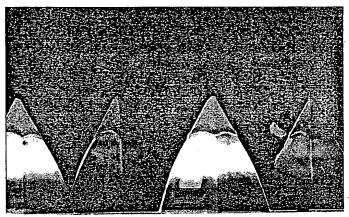


Fig. 7



238-Nov-02

000 WD11.1mm 5.00kV x2.5k 20um

Fig. 8

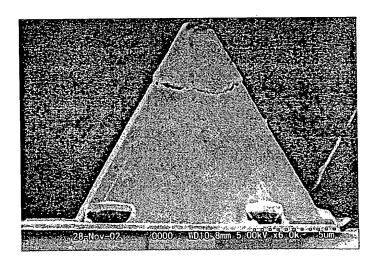


Fig. 9

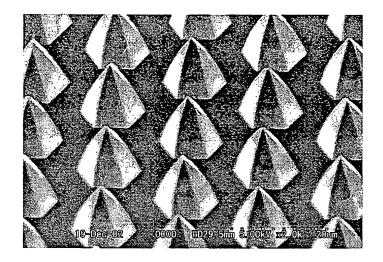


Fig. 10

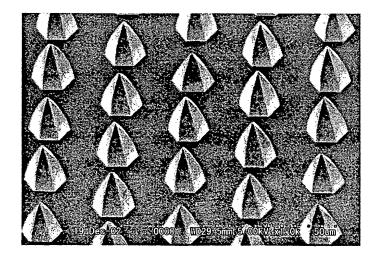


Fig. 11

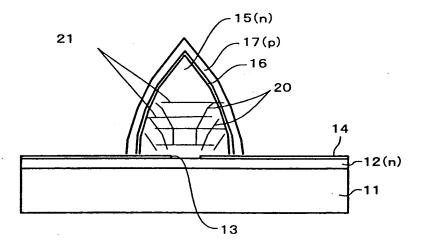


Fig. 12

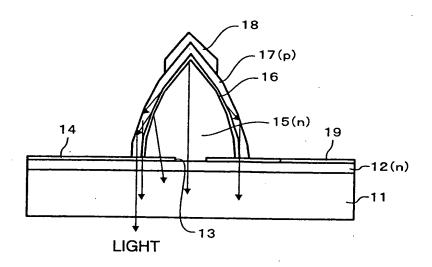


Fig. 13

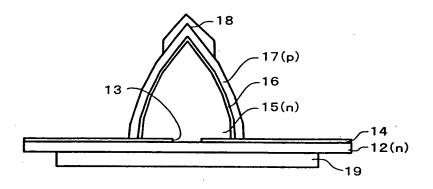


Fig. 14

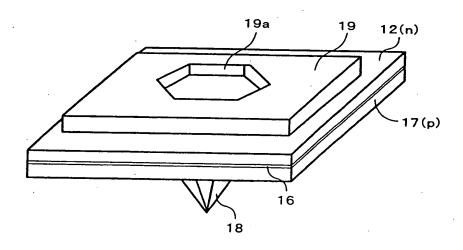
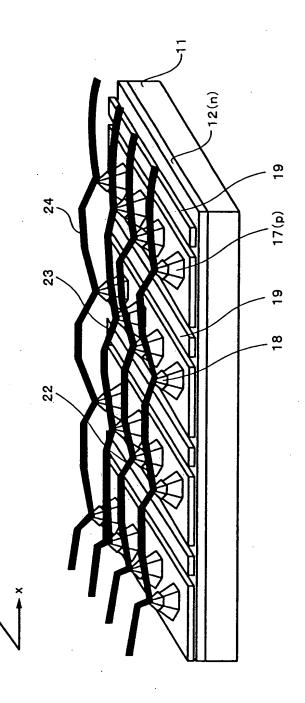
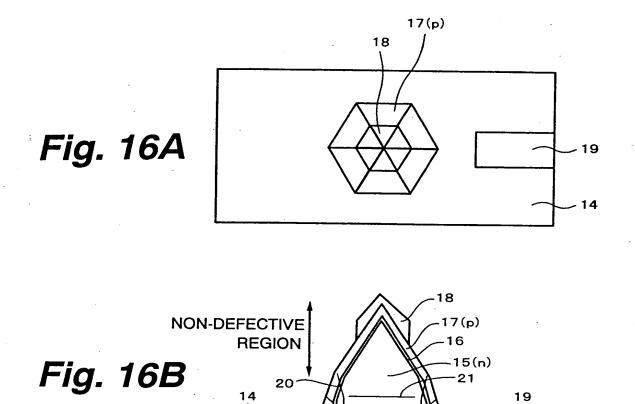


Fig. 15

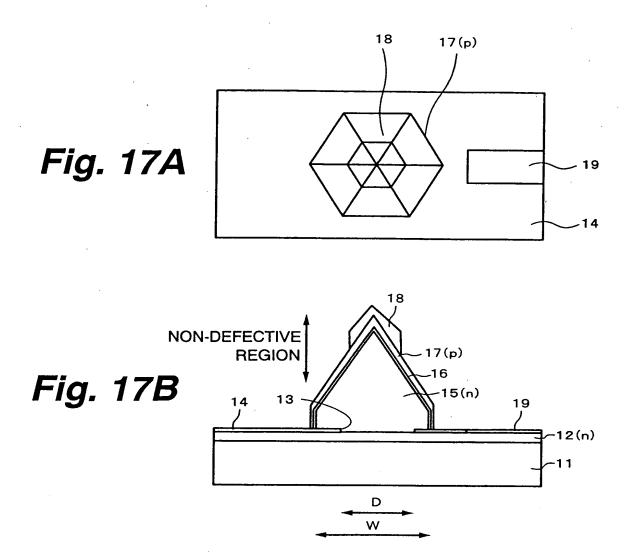


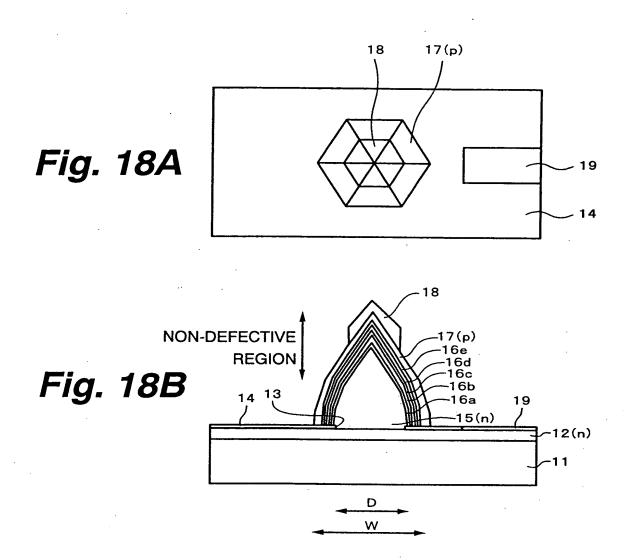
-12(n)

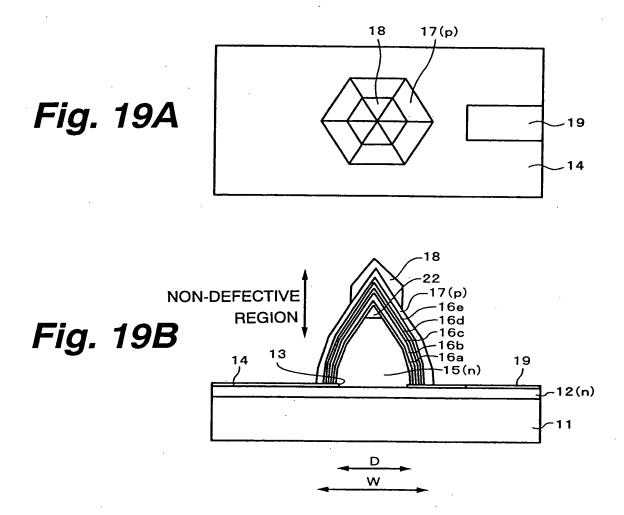
11

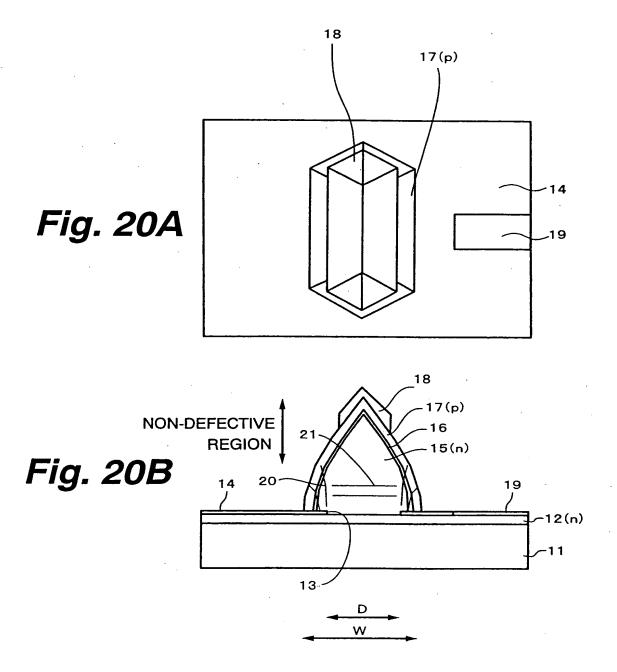


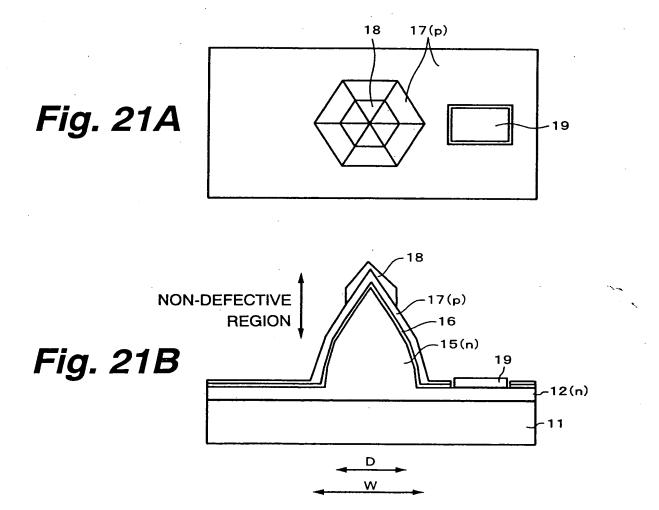
-13











DESCRIPTION OF REFERENCE NUMERALS

11	SAPPHIRE SUBSTRATE
12	n-TYPE GaN LAYER
13	OPENING
14	GROWTH MASK
15	n-TYPE GaN LAYER
16	ACTIVE LAYER
17	p-TYPE GaN LAYER
18	p-SIDE ELECTRODE
19	n-SIDE ELECTRODE